

**In the Claims:**

The following listing replaces all prior listing of claims in the application.

**Listing of Claims:**

Cancel claims 1-21.

22. (New) A patterning method, comprising:

- applying an auxiliary layer to a carrier material;
- applying a mask layer to the auxiliary layer prior to a production of a cutout;
- patterning the mask layer with a lithographic method;
- patterning the auxiliary layer and the carrier material with the production of the cutout in accordance with the cutout;
- modifying the cutout in a region of the auxiliary layer by isotropic etch-back, where the cutout in a region of the carrier material is not modified or not modified to an extent of the region of the auxiliary layer;
- filling the modified cutout with a filling material;
- removing the auxiliary layer after filling;
- patterning the carrier material using the filling material; and
- producing at least one further cutout.

23. (New). The method of claim 22, further comprising:

- planarizing the filling material prior to patterning the carrier material.

24. (New) The method of claim 22, further comprising producing a minimum feature size of less than one hundred nanometers.

25. (New) The method of claim 22, further comprising producing a minimum feature size of less than fifty nanometers.

26. (New) The method of claim 23, further comprising:

- forming a mask layer as a carrier material prior to applying the auxiliary layer;
- and

patterning a base material using the mask layer after patterning the carrier material using the filling material.

27. (New) The method claim 23, further comprising using a semiconductor material as the carrier material.

28. (New) The method of claim 27, further comprising forming at least one layer in the expanded cutout prior to filling.

29. (New) The method as claimed in claim 28, where forming at least one layer comprises the method of claim 1.

30. (New) The method of claim 27, further comprising:  
filling the cutout with a further filling material; and  
removing the filling material serving for patterning after the filling of the cutout.

31. (New) The method of claim 27, further comprising:  
partially removing the filling material from the cutout, where one part of a bottom of the cutout is uncovered and another part of a bottom of the cutout remains covered with filling material.

32. (New) The method of claim 27, further comprising:  
oxidizing the semiconductor material in the region between the cutout and the further cutout.

33. (New) A field effect transistor, comprising:  
two channel connection regions;  
a control region comprising at least two control sections;  
an active region that is formed as a projection of a monocrystalline substrate disposed between the channel connection regions and between two control region sections;  
insulating regions that are electrically insulating and are disposed between the control region sections and the active region; and

where the projection is isolated from the substrate at a base by an insulating material that is electrically insulating, and where the insulating material ends laterally at the projection in the monocrystalline substrate.

34. (New) The field effect transistor of claim 33, where two side areas of the projection that lie at the base of the projection transversely adjoin two substrate areas of the substrate that are disposed in two planes spaced apart from one another by a distance greater than one nanometer.

35. (New) The field effect transistor of claim 33, where the control region sections are formed on the two side areas of the projection.

36. (New) The field effect transistor of claim 33, where the insulating material does not project beyond at least one side area of the projection.

37. (New) The method of claim 22, where modifying the cutout comprises expanding the cutout.

38. (New) The method of claim 27, where the carrier material comprises a monocrystalline semiconductor material.

39. (New) The method of claim 28, where filling comprises filling with an electrically insulating layer and an electrically conductive layer.

40. (New) The method of claim 32, where the region comprises an intermediate region extending from the cutout to the further cutout.

41. (New) The method of claim 32, where oxidizing comprises oxidizing prior to the removal of the filling material.

42. (New) The method of claim 32, where oxidizing comprises oxidizing after the production of an oxidation protective layer on at least one sidewall of the further cutout.